

1. (Thrice Amended)

*Sub E1* A method of manufacturing a thin film resistor with a moisture barrier comprising:  
*Sub E1* depositing a non-tantalum metal film resistive layer on a thin film resistor substrate;  
*Sub E1* attaching a thin film resistor termination on each end of the metal film resistive layer; and  
*Sub E1* depositing the moisture barrier comprising a layer of tantalum pentoxide film directly overlaying  
and attaching to the metal film resistive layer to reduce failures due to electrolytic  
corrosion under powered moisture conditions.

15. (Twice Amended)

*Sub E2* A method of manufacturing a thin film resistor with a moisture barrier comprising:  
*Sub E2* depositing a non-tantalum metal film resistive layer on a substrate;  
*Sub E2* attaching a termination on each end of the metal film resistive layer;  
*Sub E2* depositing a passivation layer directly overlaying and attaching to the metal film layer; and  
*Sub E2* depositing the moisture barrier comprising a layer of tantalum pentoxide film directly overlaying  
and attaching to the passivation layer for reducing failures due to electrolytic corrosion  
under powered moisture conditions.